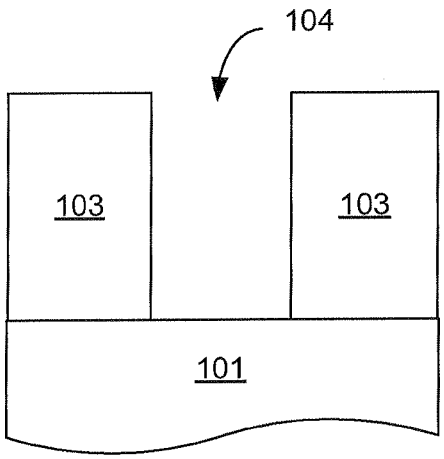



FIG. 1A

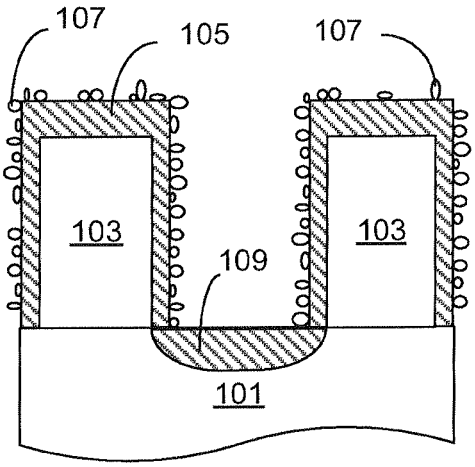



FIG. 1B

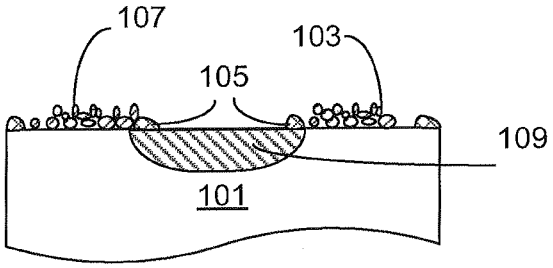



FIG. 1C

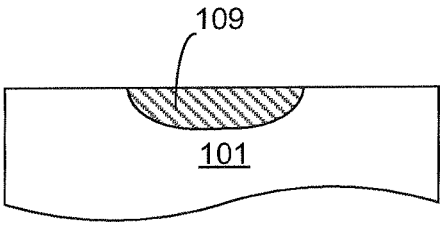



FIG. 1D

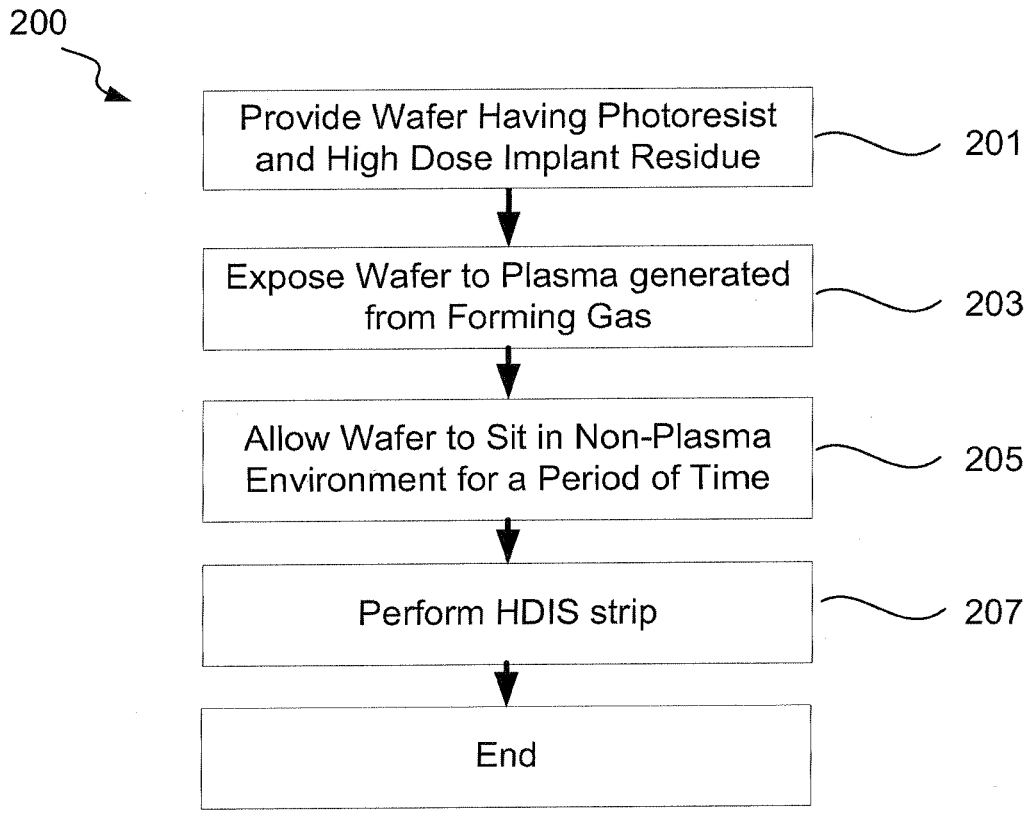

200
Provide Wafer Having Photoresist and High Dose Implant Residue
201
Expose Wafer to Plasma generated from Forming Gas
203
Allow Wafer to Sit in Non-Plasma Environment for a Period of Time
205
Perform HDIS strip
207
End

FIG. 2

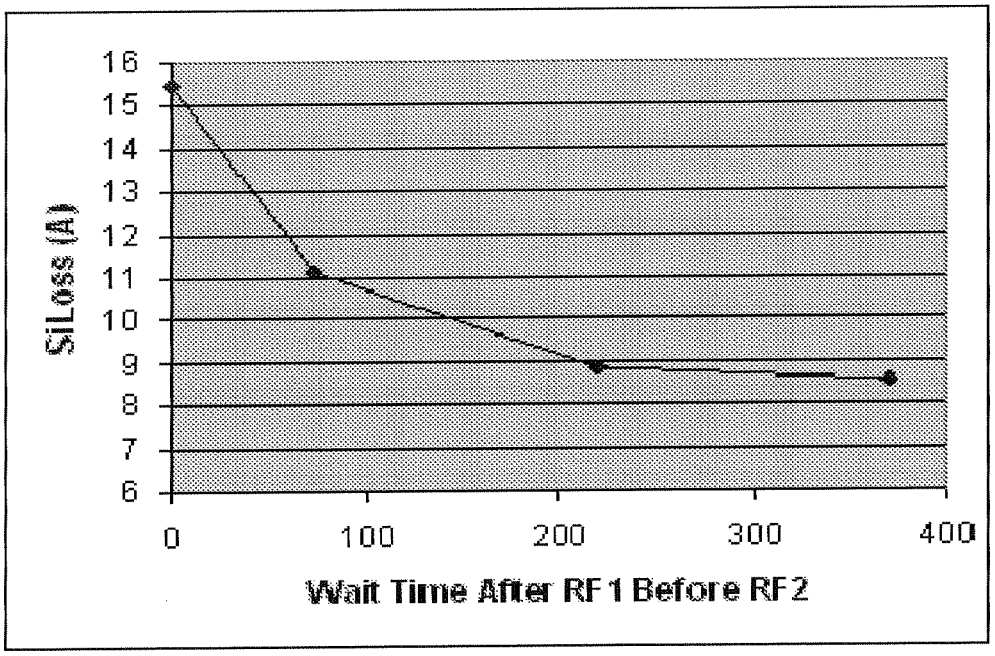

16
15
14
13
12
11
10
9
8
7
6
SiLoss (A)
0
100
200
300
400
Wait Time After RF1 Before RF2

FIG. 3

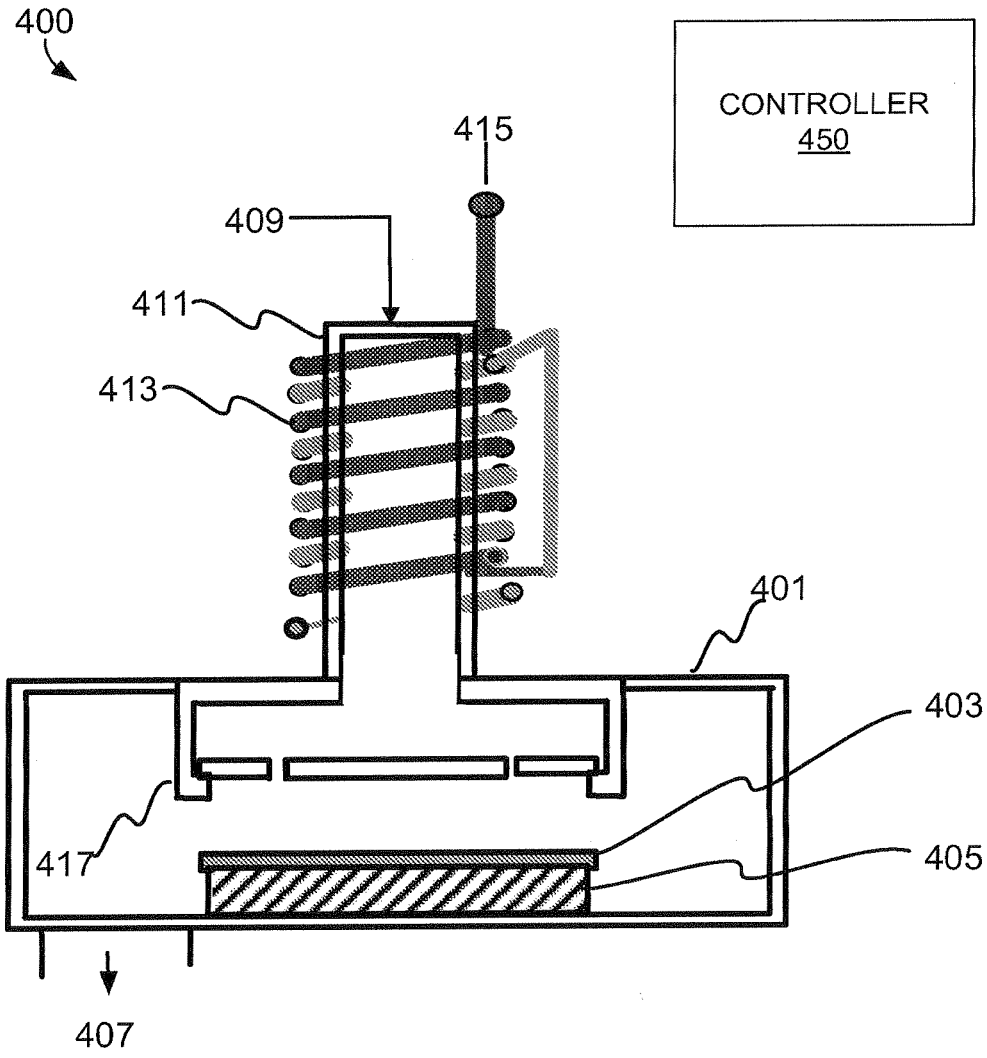



FIG. 4

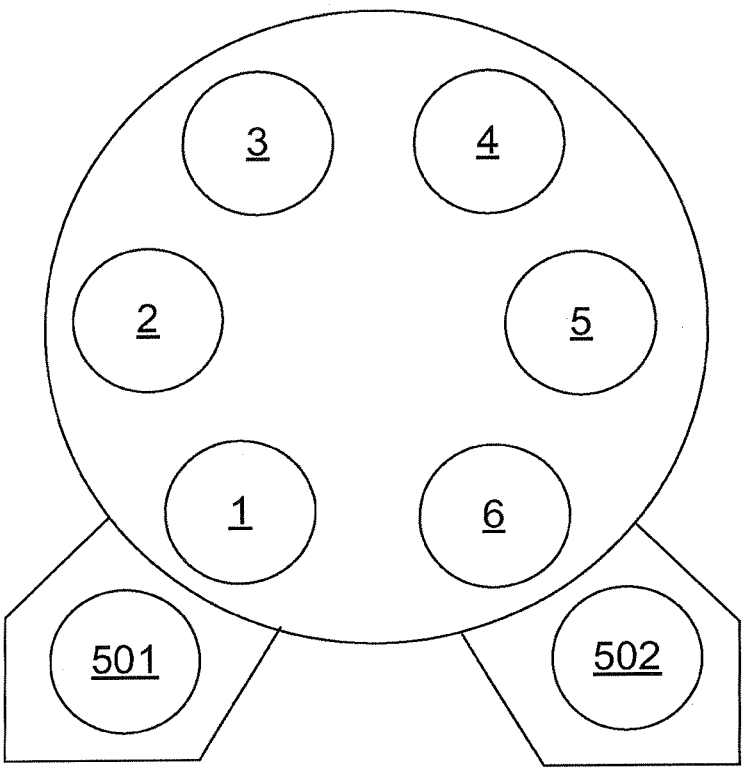



FIG. 5